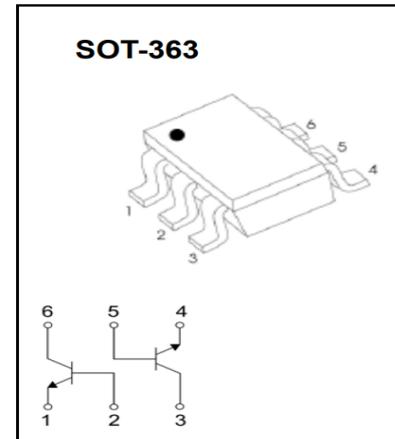


Plastic-Encapsulate Transistors

TRANSISTOR (NPN+NPN)

FEATURES

- For General AF Applications
- High Collector Current
- High Current Gain
- Low Collector-Emitter Saturation Voltage



MAXMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	50	V
V _{CEO}	Collector-Emitter Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	0.5	A
P _C	Collector Dissipation	0.2	W
R _{θJA}	Thermal Resistance from Junction to Ambient	625	°C/W
T _j	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =10μA, I _E =0	50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	45			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =1μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =20V, I _E =0			0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =1V, I _C =100mA	100		600	
	h _{FE(2)}	V _{CE} =1V, I _C =500mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA			0.7	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =500mA, I _B =50mA			1.2	V
Base-emitter voltage	V _{BE(ON)}	V _{CE} =1V, I _C =500mA			1.2	V
Transition frequency	f _T	V _{CE} =5V, I _C =10mA, f=100MHz	100			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, f=1MHz			5	pF

CLASSIFICATION of h_{FE(1)}

Rank	BC817-16DW	BC817-25DW	BC817-40DW
Range	100-250	160-400	250-600
Marking	S6A	S6B	S6C

Typical Characteristics

